

IN THE SPECIFICATION

Please replace the paragraph on page 14, lines 14-25 as follows:

Figure 7A illustrates a subsequent step of formation of the isolation trench wherein insulator island 22, spacer 28, and isolation film 36 are planarized to form a common co-planar first upper surface 38. First upper surface 38 will preferably be formed by a CMP or etchback process. Preferably, planarization will ~~be selective~~ remove isolation film 36, ~~and relatively 36~~ slightly ~~selective to~~ faster than insulator island 22, such as by a factor of about one half. A first preferred selectivity of an etch recipe used in the inventive method is in the range of about 1:1 to 2:1, ~~selective to wherein~~ isolation film 36 is removed faster as compared to insulator island. A more preferred selectivity is in the range of about 1.3:1 to about 1.7:1. A most preferred selectivity is about 1.5:1. Planarization also requires the etch recipe to ~~be slightly selective to~~ remove spacer 28 ~~over~~ slightly faster than insulator island 22. Preferably, spacer 28 and insulator film 36 are made from the same material such that the etch will be substantially uniform as to the selectivity thereof with respect to spacer 28 and isolation film 36 over insulator island 22.